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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Obsolete
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	128KB
RAM Size	16KB
Peripherals	DMA, POR, WDT
Connectivity	EBI/EMI, I²C, SPI, UART/USART
Speed	100MHz
Primary Attributes	ProASIC®3 FPGA, 60K Gates, 1536D-Flip-Flops
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a2f060m3e-1tq144i

Package I/Os: MSS + FPGA I/Os

Device	A2F060[1]			A2F200[2]				A2F500[2]			
Package	**TQ144**	**CS288**	**FG256**	**PQ208**	**CS288**	**FG256**	**FG484**	**PQ208**	**CS288**	**FG256**	**FG484**
Direct Analog Inputs	11	11	11	8	8	8	8	8	8	8	12
Shared Analog Inputs	4	4	4	16	16	16	16	16	16	16	20
Total Analog Inputs	15	15	15	24	24	24	24	24	24	24	32
Analog Outputs	1	1	1	1	2	2	2	1	2	2	3
MSS I/Os[3,4]	21[5]	28[5]	26[5]	22	31	25	41	22	31	25	41
FPGA I/Os	33[6]	68	66	66	78	66	94	66[6]	78	66	128
Total I/Os	70	112	108	113	135	117	161	113	135	117	204

Notes:

1. *There are no LVTTL capable direct inputs available on A2F060 devices.*
2. *These pins are shared between direct analog inputs to the ADCs and voltage/current/temperature monitors.*
3. *16 MSS I/Os are multiplexed and can be used as FPGA I/Os, if not needed for MSS. These I/Os support Schmitt triggers and support only LVTTL and LVCMOS (1.5 / 1.8 / 2.5, 3.3 V) standards.*
4. *9 MSS I/Os are primarily for 10/100 Ethernet MAC and are also multiplexed and can be used as FPGA I/Os if Ethernet MAC is not used in a design. These I/Os support Schmitt triggers and support only LVTTL and LVCMOS (1.5 / 1.8 / 2.5, 3.3 V standards.*
5. *10/100 Ethernet MAC is not available on A2F060.*
6. *EMC is not available on the A2F500 PQ208 and A2F060 TQ144 package.*

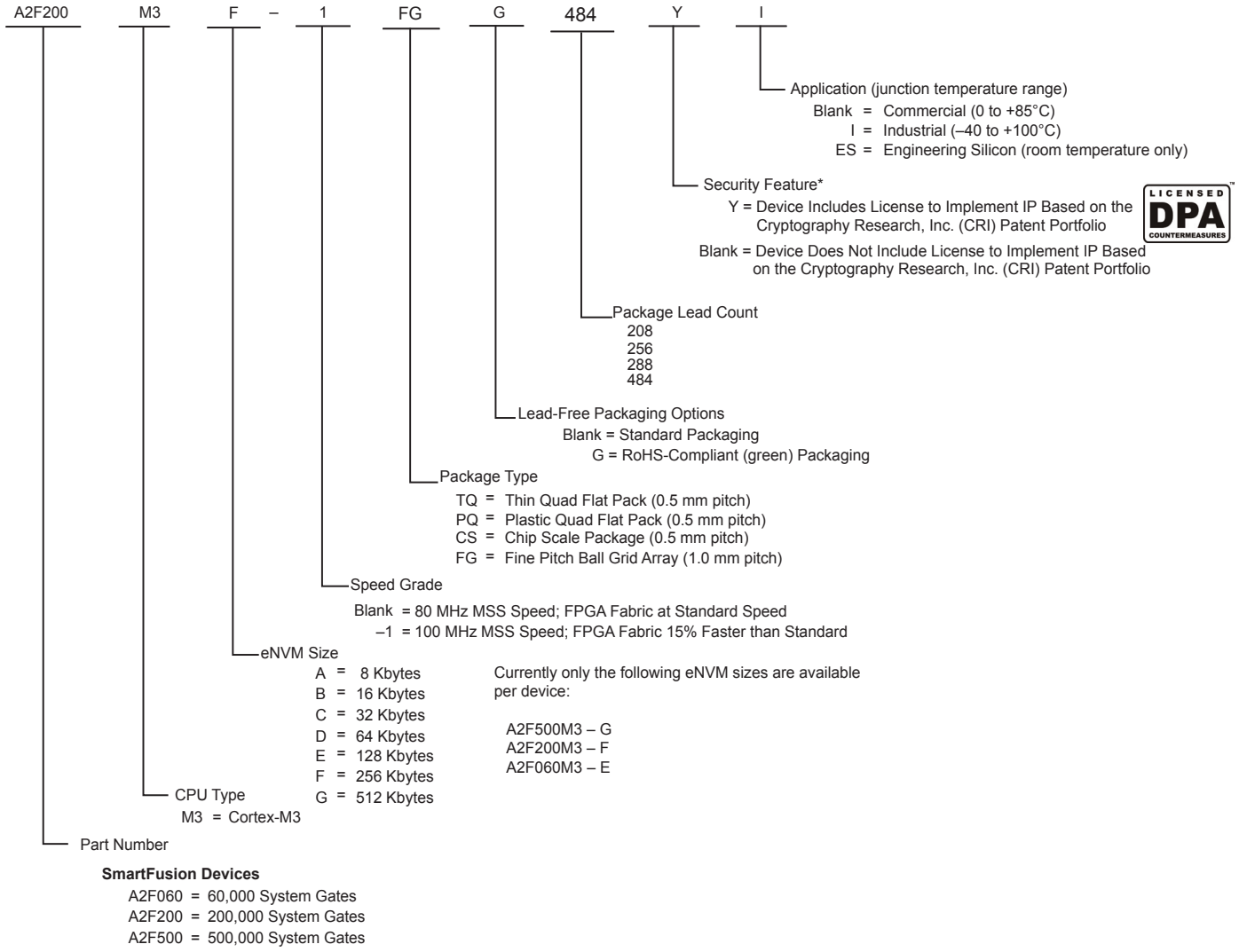
Table 1 • SmartFusion cSoC Package Sizes Dimensions

Package	TQ144	PQ208	CS288	FG256	FG484
Length × Width (mm\mm)	20 × 20	28 × 28	11 × 11	17 × 17	23 × 23
Nominal Area (mm^2)	400	784	121	289	529
Pitch (mm)	0.5	0.5	0.5	1.0	1.0
Height (mm)	1.40	3.40	1.05	1.60	2.23

SmartFusion cSoC Device Status

Device	Status
A2F060	Preliminary: CS288, FG256, TQ144
A2F200	Production: CS288, FG256, FG484, PQ208
A2F500	Production: CS288, FG256, FG484, PQ208

Product Ordering Codes



*Note: *Most devices in the SmartFusion cSoC family can be ordered with the Y suffix. Devices with a package size greater or equal to 5x5 mm are supported. Contact your local Microsemi SoC Products Group sales representative for more information.*

Temperature Grade Offerings

SmartFusion cSoC	A2F060	A2F200	A2F500
TQ144	C, I	–	–
PQ208	–	C, I	C, I
CS288	C, I	C, I	C, I
FG256	C, I	C, I	C, I
FG484	–	C, I	C, I

Notes:
1. *C = Commercial Temperature Range: 0°C to 85°C Junction*
2. *I = Industrial Temperature Range: –40°C to 100°C Junction*

SmartFusion Family Overview

SmartFusion DC and Switching Characteristics

SmartFusion Development Tools

SmartFusion Programming

Pin Descriptions

Datasheet Information

Table 2-14 • Different Components Contributing to Dynamic Power Consumption in SmartFusion cSoCs

Parameter	Definition	Power Supply		Device			Units
		Name	Domain	A2F060	A2F200	A2F500	
PAC24	Current Monitor Power Contribution	See Table 2-93 on page 2-78	–	1.03			mW
PAC25	ABPS Power Contribution	See Table 2-96 on page 2-82	–	0.70			mW
PAC26	Sigma-Delta DAC Power Contribution[2]	See Table 2-98 on page 2-85	–	0.58			mW
PAC27	Comparator Power Contribution	See Table 2-97 on page 2-84	–	1.02			mW
PAC28	Voltage Regulator Power Contribution[3]	See Table 2-99 on page 2-87	–	36.30			mW

Notes:

1. *For a different use of MSS peripherals and resources, refer to SmartPower.*
2. *Assumes Input = Half Scale Operation mode.*
3. *Assumes 100 mA load on 1.5 V domain.*

Table 2-15 • Different Components Contributing to the Static Power Consumption in SmartFusion cSoCs

Parameter	Definition	Power Supply		Device			Units
		Name	Domain	A2F060	A2F200	A2F200	
PDC1	Core static power contribution in SoC mode	VCC	1.5 V	11.10	23.70	37.95	mW
PDC2	Device static power contribution in Standby Mode	See Table 2-8 on page 2-10	–	11.10	23.70	37.95	mW
PDC3	Device static power contribution in Time Keeping mode	See Table 2-8 on page 2-10	3.3 V	33.00	33.00	33.00	µW
PDC7	Static contribution per input pin (standard dependent contribution)	VCCxxxxIOBx/VCC	See Table 2-10 and Table 2-11 on page 2-11.				
PDC8	Static contribution per output pin (standard dependent contribution)	VCCxxxxIOBx/VCC	See Table 2-12 and Table 2-13 on page 2-11.				
PDC9	Static contribution per PLL	VCC	1.5 V	2.55	2.55	2.55	mW

Table 2-16 • eNVM Dynamic Power Consumption

Parameter	Description	Condition	Min.	Typ.	Max.	Units
eNVM System	eNVM array operating power	Idle		795		µA
		Read operation	See Table 2-14 on page 2-12.			
		Erase		900		µA
		Write		900		µA
PNVMCTRL	eNVM controller operating power			20		µW/MHz

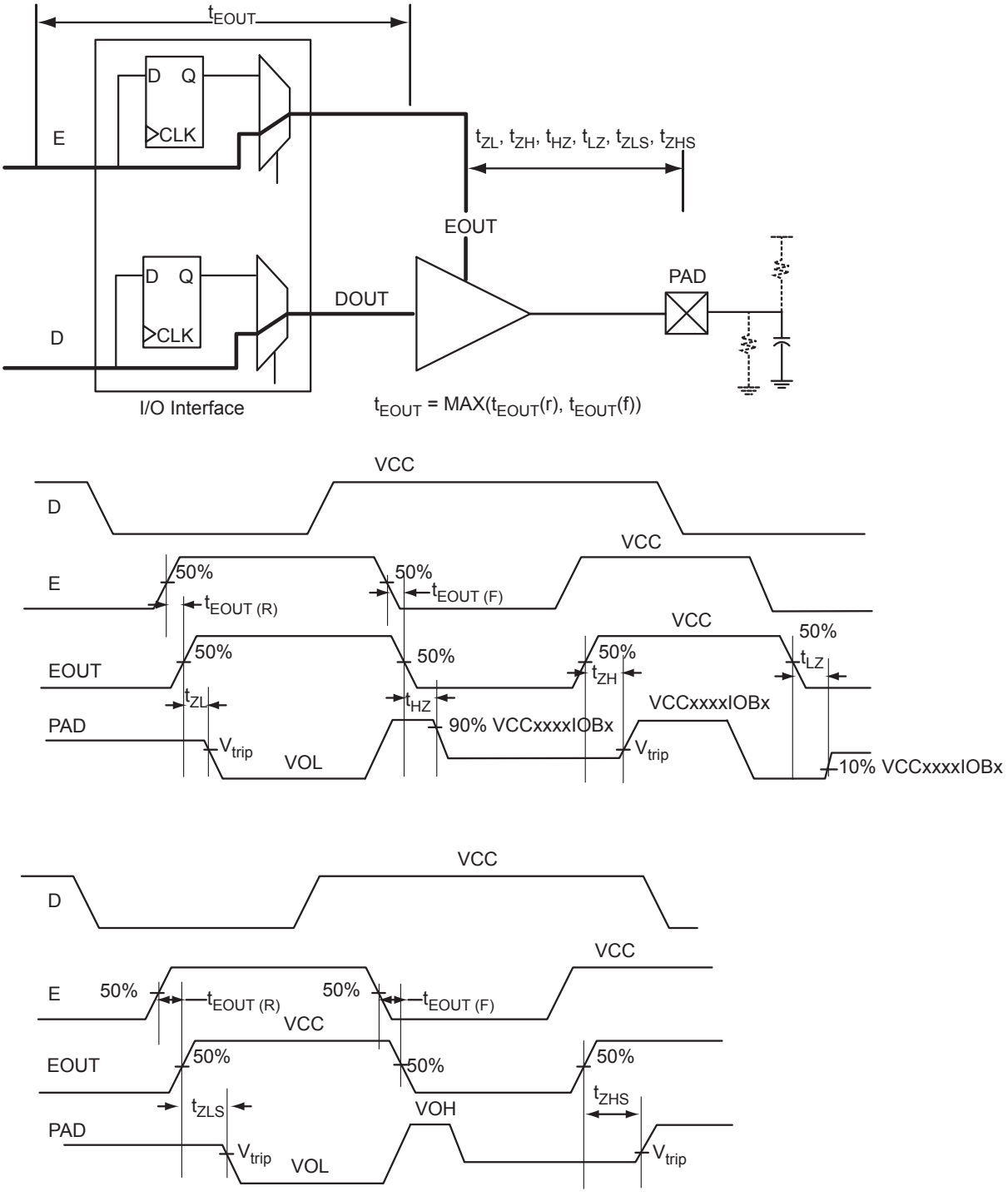


Figure 2-5 • **Tristate Output Buffer Timing Model and Delays (example)**

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-47 • Minimum and Maximum DC Input and Output Levels Applicable to FPGA I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	I_{OL}	I_{OH}	I_{OSL}	I_{OSH}	I_{IL}	I_{IH}
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
2 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	2	2	11	9	15	15
4 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	4	4	22	17	15	15
6 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	6	6	44	35	15	15
8 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	8	8	51	45	15	15
12 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	12	12	74	91	15	15
16 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	1.9	0.45	VCCxxxxIOBx – 0.45	16	16	74	91	15	15

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Software default selection highlighted in gray.*

Table 2-48 • Minimum and Maximum DC Input and Output Levels Applicable to MSS I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	I_{OL}	I_{OH}	I_{OSL}	I_{OSH}	I_{IL}	I_{IH}
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
4 mA	–0.3	0.35 * VCCxxxxIOBx	0.65 * VCCxxxxIOBx	3.6	0.45	VCCxxxxIOBx – 0.45	4	4	22	17	15	15

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Software default selection highlighted in gray.*

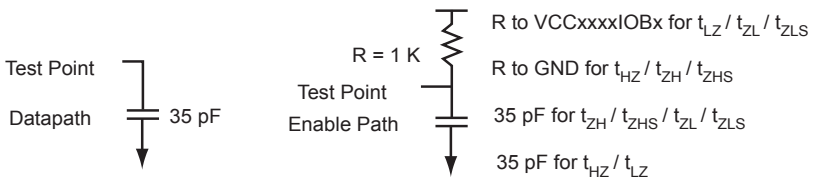


Figure 2-8 • AC Loading

Table 2-49 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	V_{REF} (typ.) (V)	C_{LOAD} (pF)
0	1.8	0.9	–	35

* *Measuring point = V_{trip}. See Table 2-22 on page 2-24 for a complete table of trip points.*

Table 2-52 • 1.8 V LVCMOS High Slew
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 1.7 V
Applicable to MSS I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	Std.	0.22	2.77	0.09	1.09	1.64	0.22	2.82	2.72	2.21	2.25	ns
	–1	0.18	2.31	0.07	0.91	1.37	0.18	2.35	2.27	1.84	1.87	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

Table 2-63 • LVDS Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Typ.	Max.	Units
VCCFPGAIOBx	Supply voltage	2.375	2.5	2.625	V
VOL	Output low voltage	0.9	1.075	1.25	V
VOH	Output high voltage	1.25	1.425	1.6	V
I_{OL}[1]	Output lower current	0.65	0.91	1.16	mA
I_{OH}[1]	Output high current	0.65	0.91	1.16	mA
VI	Input voltage	0		2.925	V
I_{IH}[2]	Input high leakage current			15	µA
I_{IL}[2]	Input low leakage current			15	µA
V_{ODIFF}	Differential output voltage	250	350	450	mV
V_{OCM}	Output common mode voltage	1.125	1.25	1.375	V
V_{ICM}	Input common mode voltage	0.05	1.25	2.35	V
V_{IDIFF}	Input differential voltage	100	350		mV

Notes:

1. *I_{OL}/I_{OH} defined by V_{ODIFF}/(resistor network).*
2. *Currents are measured at 85°C junction temperature.*

Table 2-64 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	V_{REF} (typ.) (V)
1.075	1.325	Cross point	–

* *Measuring point = V_{trip}. See Table 2-22 on page 2-24 for a complete table of trip points.*

Timing Characteristics

Table 2-65 • LVDS
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCFPGAIOBx = 2.3 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.60	1.83	0.04	1.87	ns
–1	0.50	1.53	0.03	1.55	ns

Notes:

1. *For the derating values at specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*
2. *The above mentioned timing parameters correspond to 24mA drive strength.*

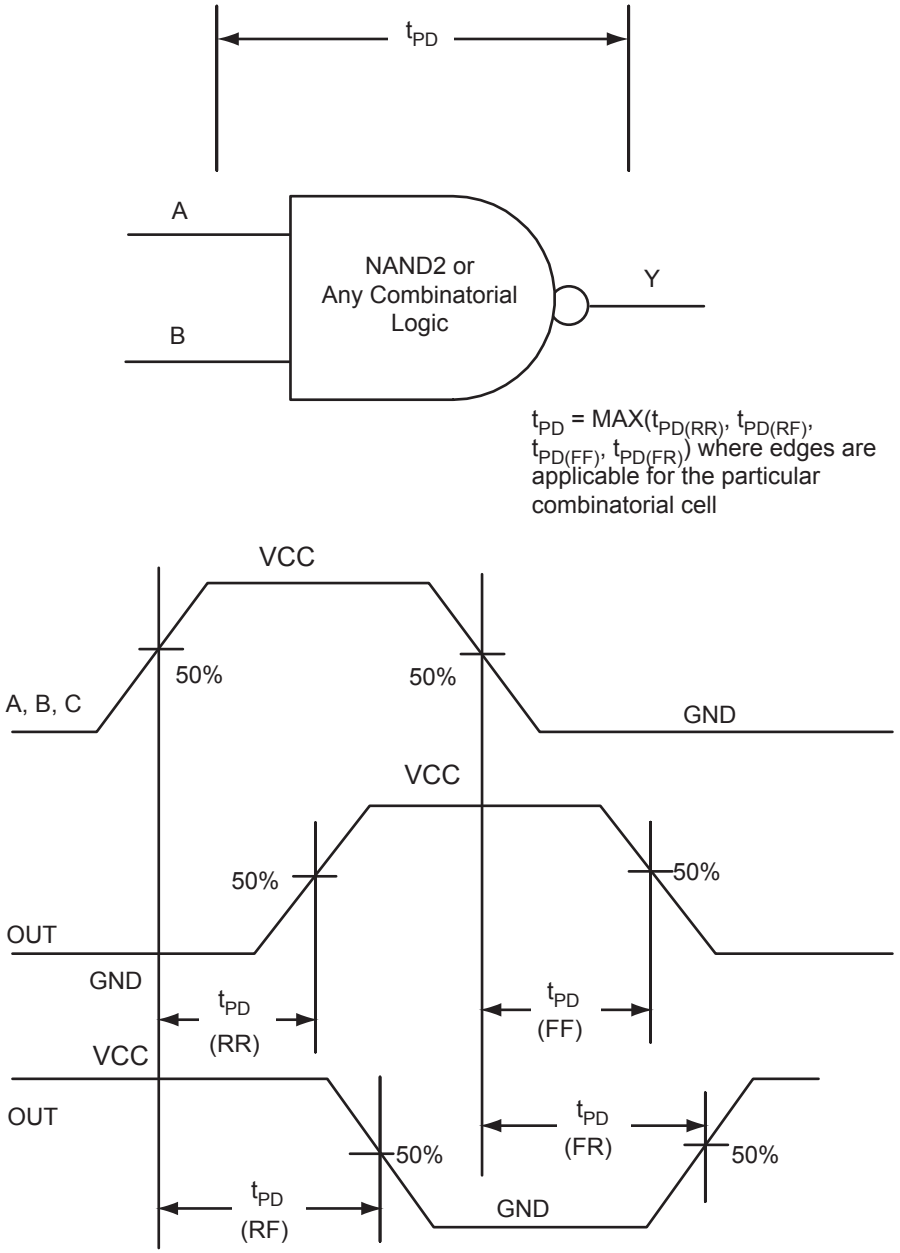


Figure 2-24 • **Timing Model and Waveforms**

Table 2-92 • JTAG 1532
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{RSTB2Q}	Reset to Q (data out)	26.67	30.67	ns
F_{TCKMAX}	TCK Maximum Frequency	19.00	21.85	MHz
$t_{TRSTREM}$	ResetB Removal Time	0.00	0.00	ns
$t_{TRSTREC}$	ResetB Recovery Time	0.27	0.31	ns
$t_{TRSTMPW}$	ResetB Minimum Pulse	TBD	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Analog Sigma-Delta Digital to Analog Converter (DAC)

Unless otherwise noted, sigma-delta DAC performance is specified at 25°C with nominal power supply voltages, using the internal sigma-delta modulators with 16-bit inputs, HCLK = 100 MHz, modulator inputs updated at a 100 KHz rate, in voltage output mode with an external 160 pF capacitor to ground, after trimming and digital [pre-]compensation.

***Table 2-98* • Analog Sigma-Delta DAC**

Specification	Test Conditions	Min.	Typ.	Max.	Units
Resolution		8		24	Bits
Output range			0 to 2.56		V
	Current output mode		0 to 256		µA
Output Impedance		6	10	12	KΩ
	Current output mode	10			MΩ
Output voltage compliance	Current output mode		0–3.0		V
	–40ºC to +100ºC	0–2.7		0–3.4	V
Gain error	Voltage output mode		0.3	±2	%
	A2F060: –40ºC to +100ºC		0.3	±2	%
	A2F200: –40ºC to +100ºC		1.2	±5.3	%
	A2F500: –40ºC to +100ºC		0.3	±2	%
	Current output mode		0.3	±2	%
	A2F060: –40ºC to +100ºC		0.3	±2	%
	A2F200: –40ºC to +100ºC		1.2	±5.3	%
	A2F500: –40ºC to +100ºC		0.3	±2	%
Output referred offset	DACBYTE0 = h'00 (8-bit)		0.25	±1	mV
	–40ºC to +100ºC		1	±2.5	mV
	Current output mode		0.3	±1	µA
	–40ºC to +100ºC		1	±2.5	µA
Integral non-linearity	RMS deviation from BFSL		0.1	0.3	% FS*
Differential non-linearity			0.05	0.4	% FS*
Analog settling time			Refer to Figure 2-44 on page 2-86		µs
Power supply rejection ratio	DC, full scale output	33	34		dB

*Note: *FS is full-scale error, defined as the difference between the actual value that triggers the transition to full-scale and the ideal analog full-scale transition value. Full-scale error equals offset error plus gain error. Refer to the Analog-to-Digital Converter chapter of the SmartFusion Programmable Analog User's Guide for more information.*

Inter-Integrated Circuit (I^2C) Characteristics

This section describes the DC and switching of the I^2C interface. Unless otherwise noted, all output characteristics given are for a 100 pF load on the pins. For timing parameter definitions, refer to Figure 2-48 on page 2-92.

***Table 2-101* • I^2C Characteristics**
Commercial Case Conditions: T_J = 85ºC, V_{DD} = 1.425 V, –1 Speed Grade

Parameter	Definition	Condition	Value	Unit
V_{IL}	Minimum input low voltage	–	See Table 2-36 on page 2-30	–
	Maximum input low voltage	–	See Table 2-36	–
V_{IH}	Minimum input high voltage	–	See Table 2-36	–
	Maximum input high voltage	–	See Table 2-36	–
V_{OL}	Maximum output voltage low	I_{OL} = 8 mA	See Table 2-36	–
I_{IL}	Input current high	–	See Table 2-36	–
I_{IH}	Input current low	–	See Table 2-36	–
V_{hyst}	Hysteresis of Schmitt trigger inputs	–	See Table 2-33 on page 2-29	V
T_{FALL}	Fall time [2]	VIHmin to VILMax, C_{load} = 400 pF	15.0	ns
		VIHmin to VILMax, C_{load} = 100 pF	4.0	ns
T_{RISE}	Rise time [2]	VILMax to VIHmin, C_{load} = 400pF	19.5	ns
		VILMax to VIHmin, C_{load} = 100pF	5.2	ns
Cin	Pin capacitance	VIN = 0, f = 1.0 MHz	8.0	pF
$R_{pull-up}$	Output buffer maximum pull-down Resistance [1]	–	50	Ω
$R_{pull-down}$	Output buffer maximum pull-up Resistance [1]	–	150	Ω
D_{max}	Maximum data rate	Fast mode	400	Kbps
t_{LOW}	Low period of I2C_x_SCL [3]	–	1	pclk cycles
t_{HIGH}	High period of I2C_x_SCL [3]	–	1	pclk cycles
$t_{HD;STA}$	START hold time [3]	–	1	pclk cycles
$t_{SU;STA}$	START setup time [3]	–	1	pclk cycles
$t_{HD;DAT}$	DATA hold time [3]	–	1	pclk cycles
$t_{SU;DAT}$	DATA setup time [3]	–	1	pclk cycles

Notes:

1. *These maximum values are provided for information only. Minimum output buffer resistance values depend on VCCxxxxIOBx, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the SoC Products Group website at http://www.microsemi.com/index.php?option=com_microsemi&Itemid=489&lang=en&view=salescontact.*
2. *These values are provided for a load of 100 pF and 400 pF. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the SoC Products Group website at http://www.microsemi.com/index.php?option=com_microsemi&Itemid=489&lang=en&view=salescontact.*
3. *For allowable Pclk configurations, refer to the Inter-Integrated Circuit (I^2C) Peripherals section in the SmartFusion Microcontroller Subsystem User's Guide.*

Re-Programming the eNVM Blocks Using the Cortex-M3

In this mode the Cortex-M3 is executing the eNVM programming algorithm from eSRAM. Since individual pages (132 bytes) of the eNVM can be write-protected, the programming algorithm software can be protected from inadvertent erasure. When reprogramming the eNVM, both MSS I/Os and FPGA I/Os are available as interfaces for sourcing the new eNVM image. The SoC Products Group provides working example projects for SoftConsole, IAR, and Keil development environments. These can be downloaded via the SoC Products Group Firmware Catalog.

Alternately, the eNVM can be reprogrammed by the Cortex-M3 via the IAP driver. This is necessary when using an encrypted image.

Secure Programming

For background, refer to the "Security in Low Power Flash Devices" chapter of the *Fusion FPGA Fabric User's Guide* on the SoC Products Group website. SmartFusion ISP behaves identically to Fusion ISP. IAP of SmartFusion cSoCs is accomplished by using the IAP driver. Only the FPGA fabric and the eNVM can be reprogrammed with the protection of security measures by using the IAP driver.

Typical Programming and Erase Times

Table 4-3 documents the typical programming and erase times for two components of SmartFusion cSoCs, FPGA fabric and eNVM, using the SoC Products Group's FlashPro hardware and software. These times will be different for other ISP and IAP methods. The **Program** action in FlashPro software includes erase, program, and verify to complete.

The typical programming (including erase) time per page of the eNVM is 8 ms.

***Table 4-3* • Typical Programming and Erase Times**

	FPGA Fabric (seconds)			eNVM (seconds)			FlashROM (seconds)		
	A2F060	**A2F200**	**A2F500**	**A2F060**	**A2F200**	**A2F500**	**A2F060**	**A2F200**	**A2F500**
Erase	21	21	21	N/A	N/A	N/A	21	21	21
Program	28	35	48	18	39	71	22	22	22
Verify	2	6	12	9	18	37	1	1	1

References

User's Guides

DirectC User's Guide

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=132588

In-System Programming (ISP) of Microsemi's Low-Power Flash Devices Using FlashPro4/3/3X

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129973

Programming Flash Devices HandBook

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129930

Application Notes on IAP Programming Technique

SmartFusion cSoC: Programming FPGA Fabric and eNVM Using In-Application Programming Interface App Note

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129818

SmartFusion cSoC: Basic Bootloader and Field Upgrade eNVM Through IAP Interface App Note

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129823

User-Defined Supply Pins

Name	Type	Polarity/ Bus Size	Description
VAREF0	Input	1	Analog reference voltage for first ADC. The SmartFusion cSoC can be configured to generate a 2.56 V internal reference that can be used by the ADC. While using the internal reference, the reference voltage is output on the VAREFOUT pin for use as a system reference. If a different reference voltage is required, it can be supplied by an external source and applied to this pin. The valid range of values that can be supplied to the ADC is 1.0 V to 3.3 V. When VAREF0 is internally generated, a bypass capacitor must be connected from this pin to ground. The value of the bypass capacitor should be between 3.3 µF and 22 µF, which is based on the needs of the individual designs. The choice of the capacitor value has an impact on the settling time it takes the VAREF0 signal to reach the required specification of 2.56 V to initiate valid conversions by the ADC. If the lower capacitor value is chosen, the settling time required for VAREF0 to achieve 2.56 V will be shorter than when selecting the larger capacitor value. The above range of capacitor values supports the accuracy specification of the ADC, which is detailed in the datasheet. Designers choosing the smaller capacitor value will not obtain as much margin in the accuracy as that achieved with a larger capacitor value. See the Analog-to-Digital Converter (ADC) section in the *SmartFusion Programmable Analog User's Guide* for more information. The SoC Products Group recommends customers use 10 µF as the value of the bypass capacitor. Designers choosing to use an external VAREF0 need to ensure that a stable and clean VAREF0 source is supplied to the VAREF0 pin before initiating conversions by the ADC. To use the internal voltage reference, the VAREFOUT pin must be connected to the appropriate ADC VAREFx input on the PCB. For example, VAREFOUT can be connected to VAREF0 only, if ADC0 alone is used. VAREFOUT can be connected to VAREF1 only, if ADC1 alone is used. VAREFOUT can be connected to VAREF2 only, if ADC2 alone is used. VAREFOUT can be connected to VAREF0, VAREF1 and VAREF2 together, if ADC0, ADC1, and ADC2 all are used.
VAREF1	Input	1	Analog reference voltage for second ADC See "VAREF0" above for more information.
VAREF2	Input	1	Analog reference voltage for third ADC See "VAREF0" above for more.
VAREFOUT	Out	1	Internal 2.56 V voltage reference output. Can be used to provide the two ADCs with a unique voltage reference externally by connecting VAREFOUT to both VAREF0 and VAREF1. To use the internal voltage reference, you must connect the VAREFOUT pin to the appropriate ADC VAREFx input—either the VAREF0 or VAREF1 pin—on the PCB.

Name	Type	Polarity/ Bus Size	Description
SPI_1_DO	Out	1	Data output. Second SPI. Can also be used as an MSS GPIO (see "GPIO_x" on page 5-6).
SPI_1_SS	Out	1	Slave select (chip select). Second SPI. Can also be used as an MSS GPIO (see "GPIO_x" on page 5-6).
Universal Asynchronous Receiver/Transmitter (UART) Peripherals			
UART_0_RXD	In	1	Receive data. First UART. Can also be used as an MSS GPIO (see "GPIO_x" on page 5-6).
UART_0_TXD	Out	1	Transmit data. First UART. Can also be used as an MSS GPIO (see "GPIO_x" on page 5-6).
UART_1_RXD	In	1	Receive data. Second UART. Can also be used as an MSS GPIO (see "GPIO_x" on page 5-6).
UART_1_TXD	Out	1	Transmit data. Second UART. Can also be used as an MSS GPIO (see "GPIO_x" on page 5-6).
Ethernet MAC			
MAC_CLK	In	Rise	Receive clock. 50 MHz ± 50 ppm clock source received from RMII PHY. Can be left floating when unused.
MAC_CRSDV	In	High	Carrier sense/receive data valid for RMII PHY Can also be used as an FPGA User IO (see "IO" on page 5-6).
MAC_MDC	Out	Rise	RMII management clock Can also be used as an FPGA User IO (see "IO" on page 5-6).
MAC_MDIO	In/Out	1	RMII management data input/output Can also be used as an FPGA User IO (see "IO" on page 5-6).
MAC_RXDx	In	2	Ethernet MAC receive data. Data recovered and decoded by PHY. The RXD[0] signal is the least significant bit. Can also be used as an FPGA User I/O (see "IO" on page 5-6).
MAC_RXER	In	HIGH	Ethernet MAC receive error. If MACRX_ER is asserted during reception, the frame is received and status of the frame is updated with MACRX_ER. Can also be used as an FPGA user I/O (see "IO" on page 5-6).
MAC_TXDx	Out	2	Ethernet MAC transmit data. The TXD[0] signal is the least significant bit. Can also be used as an FPGA user I/O (see "IO" on page 5-6).
MAC_TXEN	Out	HIGH	Ethernet MAC transmit enable. When asserted, indicates valid data for the PHY on the TXD port. Can also be used as an FPGA User I/O (see "IO" on page 5-6).

Pin Number	FG484	
	A2F200 Function	A2F500 Function
A1	GND	GND
A2	NC	NC
A3	NC	NC
A4	GND	GND
A5	EMC_CS0_N/GAB0/IO01NDB0V0	EMC_CS0_N/GAB0/IO05NDB0V0
A6	EMC_CS1_N/GAB1/IO01PDB0V0	EMC_CS1_N/GAB1/IO05PDB0V0
A7	GND	GND
A8	EMC_AB[0]/IO04NDB0V0	EMC_AB[0]/IO06NDB0V0
A9	EMC_AB[1]/IO04PDB0V0	EMC_AB[1]/IO06PDB0V0
A10	GND	GND
A11	NC	NC
A12	EMC_AB[7]/IO07PDB0V0	EMC_AB[7]/IO12PDB0V0
A13	GND	GND
A14	EMC_AB[12]/IO10NDB0V0	EMC_AB[12]/IO14NDB0V0
A15	EMC_AB[13]/IO10PDB0V0	EMC_AB[13]/IO14PDB0V0
A16	GND	GND
A17	NC	IO16NDB0V0
A18	NC	IO16PDB0V0
A19	GND	GND
A20	NC	NC
A21	NC	NC
A22	GND	GND
AA1	GPIO_4/IO43RSB4V0	GPIO_4/IO52RSB4V0
AA2	GPIO_12/IO37RSB4V0	GPIO_12/IO46RSB4V0
AA3	MAC_MDC/IO48RSB4V0	MAC_MDC/IO57RSB4V0
AA4	MAC_RXER/IO50RSB4V0	MAC_RXER/IO59RSB4V0
AA5	MAC_TXD[0]/IO56RSB4V0	MAC_TXD[0]/IO65RSB4V0
AA6	ABPS0	ABPS0
AA7	TM1	TM1
AA8	ADC1	ADC1
AA9	GND15ADC1	GND15ADC1
AA10	GND33ADC1	GND33ADC1
AA11	CM3	CM3
AA12	GNDTM1	GNDTM1

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin Number	FG484	
	A2F200 Function	A2F500 Function
B3	NC	NC
B4	NC	NC
B5	VCCFPGAIOB0	VCCFPGAIOB0
B6	EMC_RW_N/GAA1/IO00PDB0V0	EMC_RW_N/GAA1/IO02PDB0V0
B7	NC	IO04PPB0V0
B8	VCCFPGAIOB0	VCCFPGAIOB0
B9	EMC_BYTEN[0]/GAC0/IO02NDB0V0	EMC_BYTEN[0]/GAC0/IO07NDB0V0
B10	EMC_AB[2]/IO05NDB0V0	EMC_AB[2]/IO09NDB0V0
B11	EMC_AB[3]/IO05PDB0V0	EMC_AB[3]/IO09PDB0V0
B12	EMC_AB[6]/IO07NDB0V0	EMC_AB[6]/IO12NDB0V0
B13	EMC_AB[14]/IO11NDB0V0	EMC_AB[14]/IO15NDB0V0
B14	EMC_AB[15]/IO11PDB0V0	EMC_AB[15]/IO15PDB0V0
B15	VCCFPGAIOB0	VCCFPGAIOB0
B16	EMC_AB[18]/IO13NDB0V0	EMC_AB[18]/IO18NDB0V0
B17	EMC_AB[19]/IO13PDB0V0	EMC_AB[19]/IO18PDB0V0
B18	VCCFPGAIOB0	VCCFPGAIOB0
B19	GBB0/IO18NDB0V0	GBB0/IO24NDB0V0
B20	GBB1/IO18PDB0V0	GBB1/IO24PDB0V0
B21	GND	GND
B22	GBA2/IO20PDB1V0	GBA2/IO27PDB1V0
C1	EMC_DB[14]/GAB2/IO71NDB5V0	EMC_DB[14]/GAB2/IO88NDB5V0
C2	NC	NC
C3	NC	NC
C4	NC	IO01NDB0V0
C5	NC	IO01PDB0V0
C6	EMC_CLK/GAA0/IO00NDB0V0	EMC_CLK/GAA0/IO02NDB0V0
C7	NC	IO03PPB0V0
C8	NC	IO04NPB0V0
C9	EMC_BYTEN[1]/GAC1/IO02PDB0V0	EMC_BYTEN[1]/GAC1/IO07PDB0V0
C10	EMC_OEN1_N/IO03PDB0V0	EMC_OEN1_N/IO08PDB0V0
C11	GND	GND
C12	VCCFPGAIOB0	VCCFPGAIOB0
C13	EMC_AB[8]/IO08NDB0V0	EMC_AB[8]/IO13NDB0V0
C14	EMC_AB[16]/IO12NDB0V0	EMC_AB[16]/IO17NDB0V0

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin Number	FG484	
	A2F200 Function	A2F500 Function
L9	VCC	VCC
L10	GND	GND
L11	VCC	VCC
L12	GND	GND
L13	VCC	VCC
L14	GND	GND
L15	VCC	VCC
L16	GND	GND
L17	GNDQ	GNDQ
L18	GDA2/IO33NDB1V0	GDA2/IO42NDB1V0
L19	VCCFPGAIOB1	VCCFPGAIOB1
L20	GDB1/IO30PDB1V0	GDB1/IO39PDB1V0
L21	GDB0/IO30NDB1V0	GDB0/IO39NDB1V0
L22	GDC2/IO32PDB1V0	GDC2/IO41PDB1V0
M1	NC	IO71PDB5V0
M2	NC	IO71NDB5V0
M3	VCCFPGAIOB5	VCCFPGAIOB5
M4	NC	IO72NPB5V0
M5	GNDQ	GNDQ
M6	NC	IO68PDB5V0
M7	GND	GND
M8	VCC	VCC
M9	GND	GND
M10	VCC	VCC
M11	GND	GND
M12	VCC	VCC
M13	GND	GND
M14	VCC	VCC
M15	GND	GND
M16	VCCFPGAIOB1	VCCFPGAIOB1
M17	NC	NC
M18	GDB2/IO33PDB1V0	GDB2/IO42PDB1V0
M19	VJTAG	VJTAG
M20	GND	GND

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Revision	Changes	Page
Revision 3 (continued)	In Table 2-3 • Recommended Operating Conditions[5,6], the VDDBAT recommended operating range was changed from "2.97 to 3.63" to "2.7 to 3.63" (SAR 25246). Recommended operating range was changed to "3.15 to 3.45" for the following voltages: VCC33A VCC33ADCx VCC33AP VCC33SDDx VCCMAINXTAL VCCLPXTAL Two notes were added to the table (SAR 27109): 1. *The following 3.3 V supplies should be connected together while following proper noise filtering practices: VCC33A, VCC33ADCx, VCC33AP, VCC33SDDx, VCCMAINXTAL, and VCCLPXTAL.* 2. *The following 1.5 V supplies should be connected together while following proper noise filtering practices: VCC, VCC15A, and VCC15ADCx.*	2-3
	In Table 2-3 • Recommended Operating Conditions[5,6], the description for VCCLPXTAL was corrected to change "32 Hz" to "32 KHz" (SAR 27110).	2-3
	The "Power Supply Sequencing Requirement" section is new (SAR 27178).	2-4
	Table 2-8 • Power Supplies Configuration was revised to change most on/off entries to voltages. Note 5 was added, stating that "on" means proper voltage is applied. The values of 6 µA and 16 µA were removed for IDC1 and IDC2 for 3.3 V. A note was added for IDC1 and IDC2: "Power mode and Sleep mode are consuming higher current than expected in the current version of silicon. These specifications will be updated when new version of the silicon is available" (SAR 27926).	2-10
	The "Power-Down and Sleep Mode Implementation" section is new (SAR 27178).	2-11
	A note was added to Table 2-86 • SmartFusion CCC/PLL Specification, pertaining to f_{out_CCC}, stating that "one of the CCC outputs (GLA0) is used as an MSS clock and is limited to 100 MHz (maximum) by software" (SAR 26388).	2-63
	Table 2-90 • eNVM Block Timing, Worst Commercial Case Conditions: T_J = 85°C, VCC = 1.425 V was revised. Values were included for A2F200 and A2F500, for –1 and Std. speed grades. A note was added to define 6:1:1:1 and 5:1:1:1 (SAR 26166).	2-76
	The units were corrected (mV instead of V) for input referred offset voltage, GDEC[1:0] = 00 in Table 2-96 • ABPS Performance Specifications (SAR 25381).	2-82
	The test condition values for operating current (ICC33A, typical) were changed in Table 2-99 • Voltage Regulator (SAR 26465).	2-87
	Figure 2-45 • Typical Output Voltage was revised to add legends for the three curves, stating the load represented by each (SAR 25247).	2-88
	The "SmartFusion Programming" chapter was moved to this document from the SmartFusion Subsystem Microcontroller User's Guide (SAR 26542). The "Typical Programming and Erase Times" section was added to this chapter.	4-7
	Figure 4-1 • TRSTB Logic was revised to change 1.5 V to "VJTAG (1.5 V to 3.3 V nominal)" (SAR 24694).	4-8

Revision	Changes	Page
	The A2F060 device was added to product information tables.	N/A
	The "Product Ordering Codes" table was updated to removed Std. speed and add speed grade 1. Pre-production was removed from the application ordering code category.	VI
	The "SmartFusion cSoC Block Diagram" was revised.	IV
	The "Datasheet Categories" section was updated, referencing the "SmartFusion cSoC Block Diagram" table, which is new.	1-4, IV
	The "VCCI" parameter was renamed to "VCCxxxxIOBx." "Advanced I/Os" were renamed to "FPGA I/Os." Generic pin names that represent multiple pins were standardized with a lower case x as a placeholder. For example, VAREFx designates VAREF0, VAREF1, and VAREF2. Modes were renamed as follows: Operating mode was renamed to SoC mode. 32KHz Active mode was renamed to Standby mode. Battery mode was renamed to Time Keeping mode. Table entries have been filled with values as data has become available.	N/A
	Table 2-1 • Absolute Maximum Ratings, Table 2-2 • Analog Maximum Ratings, and Table 2-3 • Recommended Operating Conditions[5,6] were revised extensively.	2-1 through 2-3
	Device names were updated in Table 2-6 • Package Thermal Resistance.	2-7
	Table 2-8 • Power Supplies Configuration was revised extensively.	2-10
	Table 2-11 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings was revised extensively.	2-11
	Removed "Example of Power Calculation."	N/A
	Table 2-14 • Different Components Contributing to Dynamic Power Consumption in SmartFusion cSoCs was revised extensively.	2-12
	Table 2-15 • Different Components Contributing to the Static Power Consumption in SmartFusion cSoCs was revised extensively.	2-13
	The "Power Calculation Methodology" section was revised.	2-14
	Table 2-83 • Electrical Characteristics of the RC Oscillator was revised extensively.	2-61
	Table 2-85 • Electrical Characteristics of the Low Power Oscillator was revised extensively.	2-62
	The parameter t_{RSTBQ} was changed to T_{C2CWRH} in Table 2-87 • RAM4K9.	2-69
	The 12-bit mode row for integral non-linearity was removed from Table 2-95 • ADC Specifications. The typical value for 10-bit mode was revised. The table note was punctuated correctly to make it clear.	2-81
	Figure 37-34 • Write Access after Write onto Same Address, Figure 37-34 • Read Access after Write onto Same Address, and Figure 37-34 • Write Access after Read onto Same Address were deleted.	N/A
	Table 2-99 • Voltage Regulator was revised extensively.	2-87
	The "Serial Peripheral Interface (SPI) Characteristics" section and "Inter-Integrated Circuit (I^2C) Characteristics" section are new.	2-89, 2-91